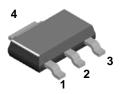
June 2007



BSP51 NPN Darlington Transistor

This device is designed for applications requiring extremly high current gain at collector currents to 500mA. Sourced from process 03.



SOT-223

1. Base 2. Collector 3. Emitter

Absolute Maximum Ratings * T_a = 25°C unless otherwise noted

| Symbol | Parameter | Value | Units |
|----------------------------------|---|------------|-------|
| V _{CES} | Collector-Emitter Voltage | 80 | V |
| V _{CBO} | Collector-Base Voltage | 90 | V |
| V _{EBO} | Emitter-Base Voltage | 5.0 | V |
| I _C | Collector Current (Continuous) | 500 | mA |
| T _{J,} T _{STG} | Junction Temperature, Storage Temperature | -55 ~ +150 | °C |

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics $T_a = 25^{\circ}C$ unless otherwise noted

| bol Parameter | Test Condition | MIN | MAX | Units |
|---------------|----------------|-----|-----|-------|
|---------------|----------------|-----|-----|-------|

Off Characteristics

| V(BR)CBO | Collector-Base Breakdown Voltage | $Ic = 100 \ \mu A, I_E = 0$ | 90 | | V |
|----------|----------------------------------|---|-----|----|----|
| V(BR)EBO | Emitter-Base Breakdown Voltage | $I_E = 10 \ \mu A, \ I_C = 0$ | 5.0 | | V |
| ICES | Collector Cutoff Current | Vce = 80 V, Ibe = 0 | | 10 | μA |
| Іево | Emitter Cutoff Current | V _{EB} = 4.0 V, I _C = 0 | | 10 | μΑ |

On Characteristics

| hfe | | Ic = 150 mA, Vce = 10 V Ic = 500 mA, Vce = 10 V | 1000 2000 | | |
|----------|--|--|--------------|-----|---|
| VCE(sat) | Collector-Emitter Saturation Voltage * | $Ic = 500 \text{ mA}, I_B = 0.5 \text{ mA}$ | | 1.3 | V |
| VBE(sat) | Base-Emitter Saturation Voltage * | $I_{C} = 500 \text{ mA}, I_{B} = 0.5 \text{ mA}$ | | 1.9 | V |

* Pulse Test: Pulse Width≤300µs, Duty Cycle≤2%

| Symbol | Characteristic | Мах | Units |
|--------|---|------|-------|
| PD | Total Device Dissipation | 1000 | mW |
| | Derate above 25° | 8.0 | mW/°C |
| R 🛛 JA | Thermal Resistance, Junction to Ambient | 125 | °C/W |

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06".



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